TRANSISTOR WITH COMMON BASE REGION

Abstract of the Disclosure

A transistor (200) comprises a single, common base region (202). One or more source regions (112) are formed in the base region (202). One or more gate regions (120) overly the common base (202) and the source regions (112). In an alternate embodiment, the gate regions (320) have a raised central portion (321). In yet another embodiment, certain source regions (402) are cross connected (404). Additionally, a polysilicon pattern (602) may be used which provides a gate finger feed network (614, 616,618), and gate fingers (604, 606, 608, 620) having length less than one half of the longest die dimension.

FIG. 2 accompanies this abstract.